

# DRA5115T

## Silicon PNP epitaxial planar type

For digital circuits

Complementary to DRC5115T

DRA2115T in SMini3 type package

### ■ Features

- High forward current transfer ratio  $h_{FE}$  with excellent linearity
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

### ■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

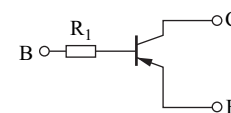
| Parameter                             | Symbol    | Rating      | Unit             |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | $V_{CBO}$ | -50         | V                |
| Collector-emitter voltage (Base open) | $V_{CEO}$ | -50         | V                |
| Collector current                     | $I_C$     | -100        | mA               |
| Total power dissipation               | $P_T$     | 150         | mW               |
| Junction temperature                  | $T_j$     | 150         | $^\circ\text{C}$ |
| Storage temperature                   | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$ |

### ■ Package

- Code  
SMini3-F2-B
- Pin Name  
1: Base  
2: Emitter  
3: Collector

### ■ Marking Symbol: LT

### ■ Internal Connection

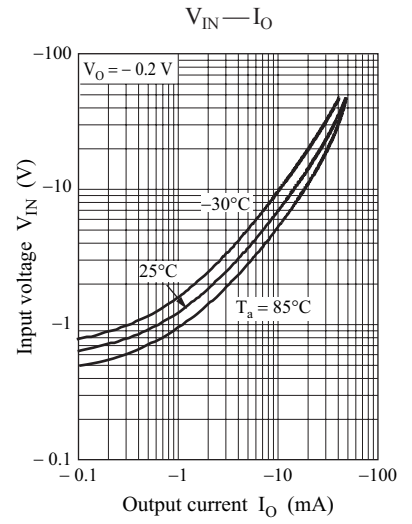
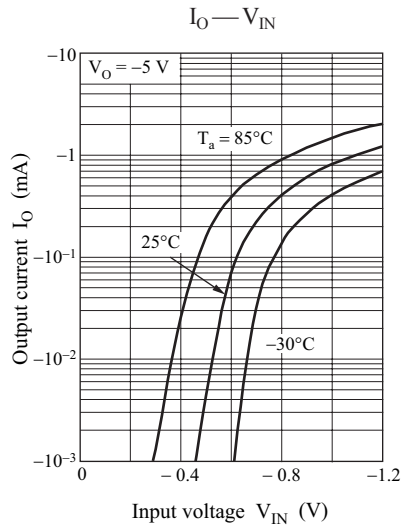
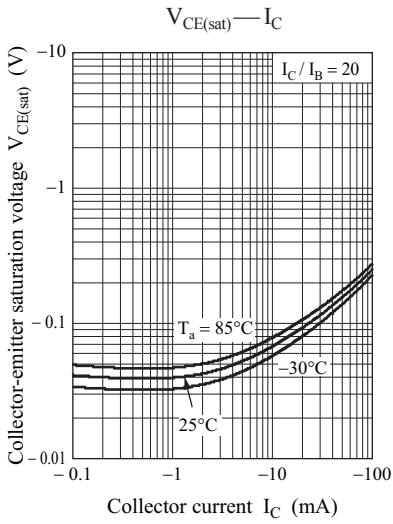
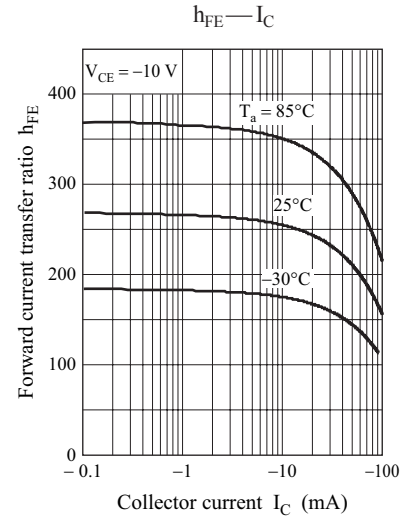
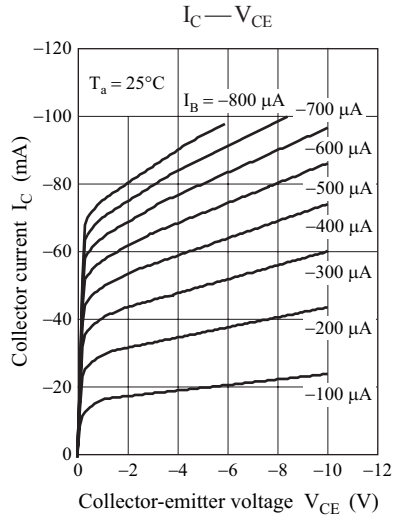
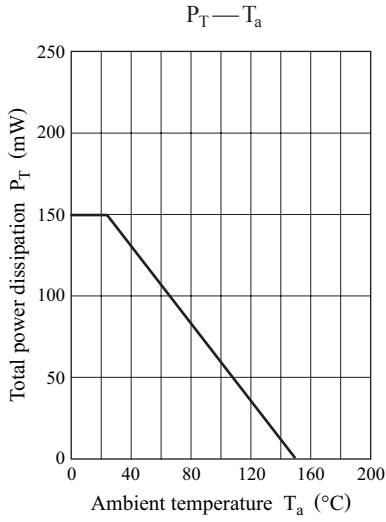


| Resistance value | $R_1$ | 100 | $k\Omega$ |
|------------------|-------|-----|-----------|
|------------------|-------|-----|-----------|

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

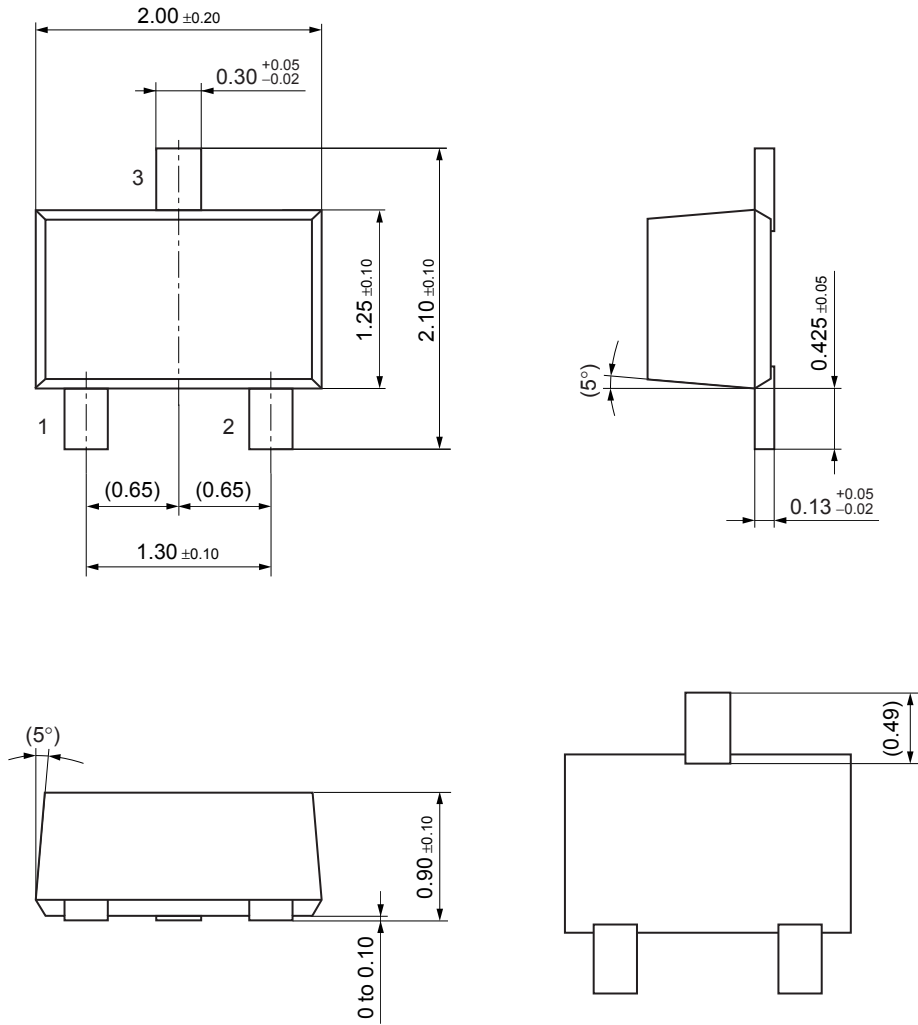
| Parameter                                    | Symbol        | Conditions                                     | Min  | Typ | Max   | Unit          |
|--|---------------|--|------|-----|-------|---------------|
| Collector-base voltage (Emitter open)        | $V_{CBO}$     | $I_C = -10 \mu\text{A}, I_E = 0$               | -50  |     |       | V             |
| Collector-emitter voltage (Base open)        | $V_{CEO}$     | $I_C = -2 \text{mA}, I_B = 0$                  | -50  |     |       | V             |
| Collector-base cutoff current (Emitter open) | $I_{CBO}$     | $V_{CB} = -50 \text{V}, I_E = 0$               |      |     | -0.1  | $\mu\text{A}$ |
| Collector-emitter cutoff current (Base open) | $I_{CEO}$     | $V_{CE} = -50 \text{V}, I_B = 0$               |      |     | -0.5  | $\mu\text{A}$ |
| Emitter-base cutoff current (Collector open) | $I_{EBO}$     | $V_{EB} = -6 \text{V}, I_C = 0$                |      |     | -0.01 | mA            |
| Forward current transfer ratio               | $h_{FE}$      | $V_{CE} = -10 \text{V}, I_C = -5 \text{mA}$    | 160  |     | 460   | —             |
| Collector-emitter saturation voltage         | $V_{CE(sat)}$ | $I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$    |      |     | -0.25 | V             |
| Input voltage (ON)                           | $V_{I(on)}$   | $V_{CE} = -0.2 \text{V}, I_C = -5 \text{mA}$   | -4.3 |     |       | V             |
| Input voltage (OFF)                          | $V_{I(off)}$  | $V_{CE} = -5 \text{V}, I_C = -100 \mu\text{A}$ |      |     | -0.4  | V             |
| Input resistance                             | $R_1$         |  | -30% | 100 | +30%  | $k\Omega$     |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SMini3-F2-B

Unit: mm



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